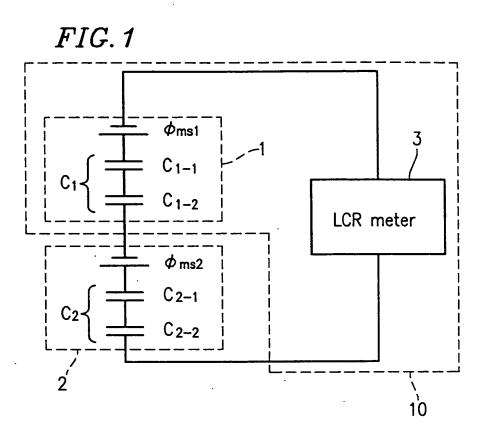
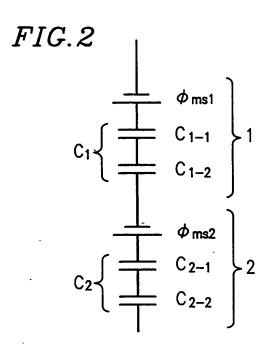
Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 1 of 9 Atty. Dkt.: 829-593

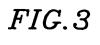


Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 2 of 9 Atty. Dkt.: 829-593

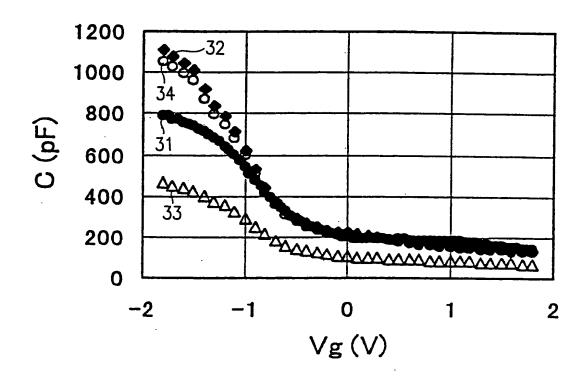


Inventor: OHMINAMI, Nobuyuki

SN unknown/Sheet 3 of 9 Atty. Dkt.: 829-593



NMOS C-V Characteristics



- 3.2nmC-V measured curve
- 2nmC-V ideal curve
- -∆— Synthesis curve -O— 2nmC−V conversion curve

Serially connect MOS structure to be measured to capacitance structure having known capacitance

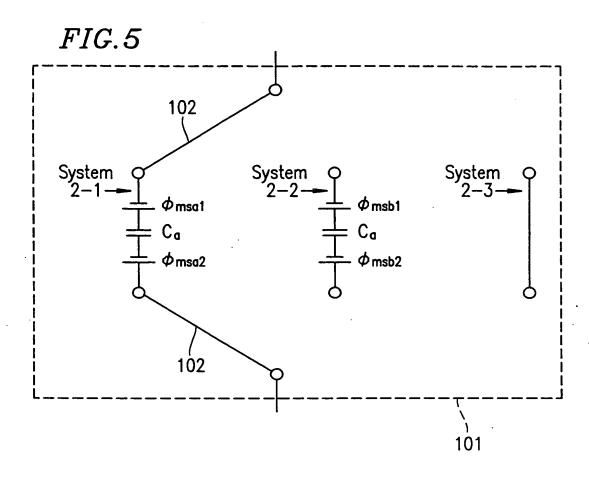
Measure synthesis capacitance of serially—connected MOS structure and capacitance structure

Calculate capacitance of MOS structure based on measured synthesis capacitance

END

S401

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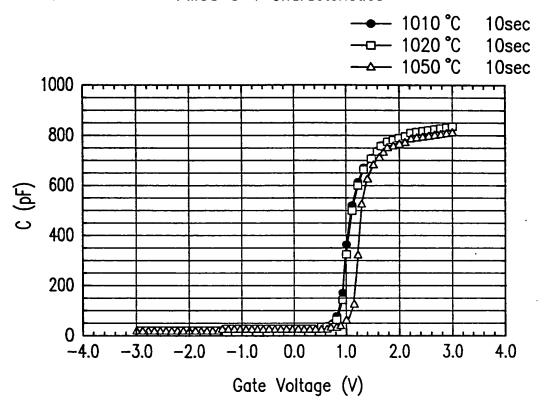


Inventor: OHMINAMI, Nobuyuki

SN unknown/Sheet 6 of 9 Atty. Dkt.: 829-593



PMOS C-V Characteristics



Active Area: 9E-4cm²

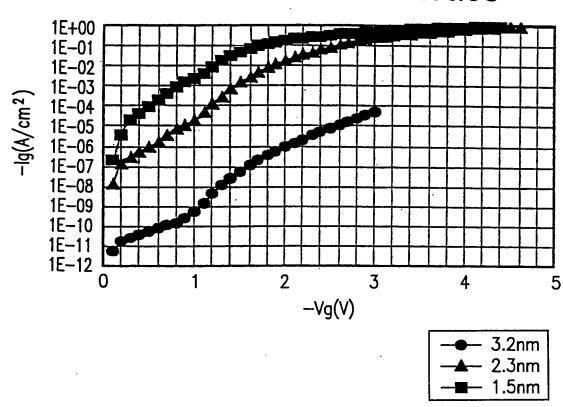
w/o Well Imp. Gate SiON: NO/N2

poly Si: 200nm P+lmp.: BF₂

01R00422

FIG.7

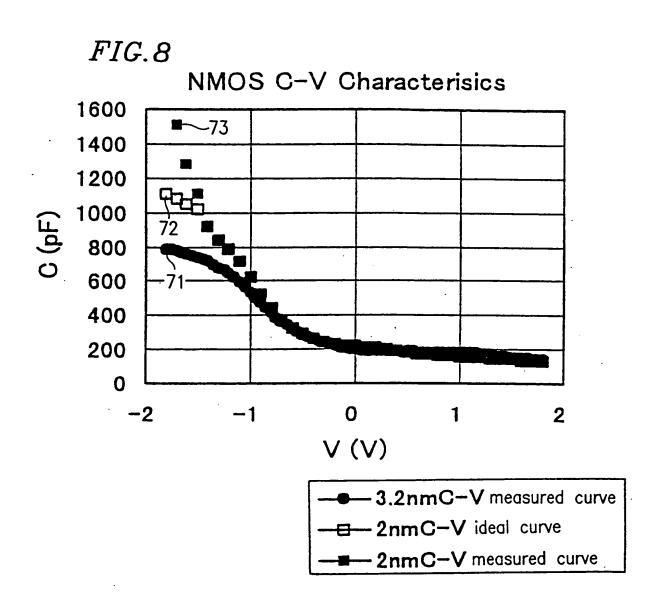
NMOS I-V Characteristics



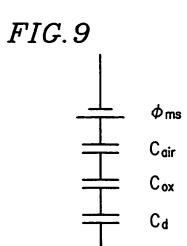
togoses atensor

Inventor: OHMINAMI, Nobuyuki









Inventor: OHMINAMI, Nobuyuki SN unknown/Sheet 9 of 9 Atty. Dkt.: 829-593